

Description

The 60N03DF is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 60N03DF meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

V_{DS} 30 V
 I_D 60 A
 $R_{DS(ON)}$ 7 m Ω

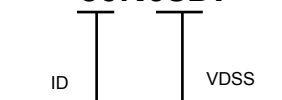
Features

Super Low Gate Charge
100% EAS Guaranteed
Green Device Available
Excellent CdV/dt effect decline
Advanced high cell density Trench technology

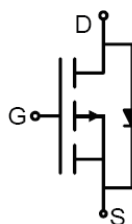
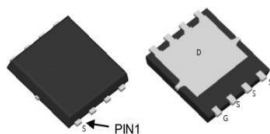


LOGO GK XXX CODE

60N03DF



PDFN3X3-8L top&bottom view Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	60		A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	33		A
I_{DM}	Pulsed Drain Current ²	198		A
EAS	Single Pulse Avalanche Energy ³	36		mJ
I_{AS}	Avalanche Current	53.8		A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	32.5		W
T_{STG}	Storage Temperature Range	-55 to 175		$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175		$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.56	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =25A	-	7	8	mΩ
		V _{GS} =4.5V, I _D =15A	-	10	14	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	1140	-	pF
C _{oss}	Output Capacitance		-	175	-	pF
C _{rss}	Reverse Transfer Capacitance		-	151	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =25A, V _{GS} =10V	-	13.3	-	nC
Q _{gs}	Gate-Source Charge		-	3.1	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =25A, R _{GEN} =3Ω, V _{GS} =10V	-	15	-	ns
t _r	Turn-on Rise Time		-	19	-	ns
t _{d(off)}	Turn-off Delay Time		-	35	-	ns
t _f	Turn-off Fall Time		-	21	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F =30A, dI/dt=100A/μs	-	25	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	26	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=15V$, $V_G=10V$, $R_G=25\Omega$, $L=0.5mH$, $I_{AS}=12A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

RATING AND CHARACTERISTIC CURVES

Figure 1: Output Characteristics

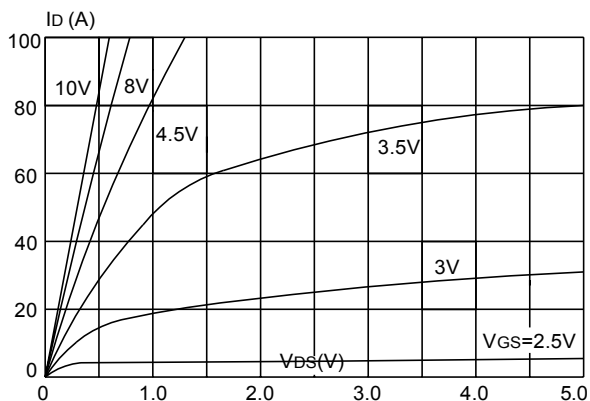


Figure 2: Typical Transfer Characteristics

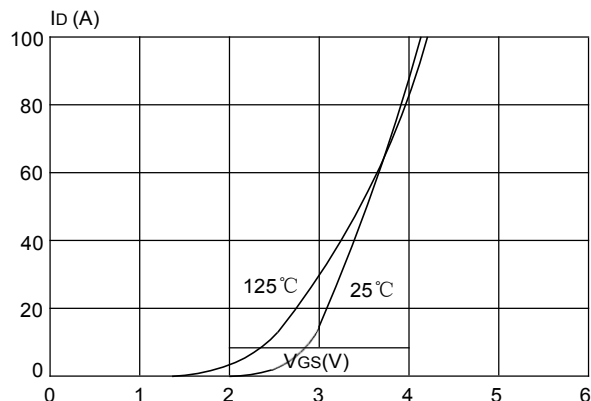


Figure 3: On-resistance vs. Drain Current

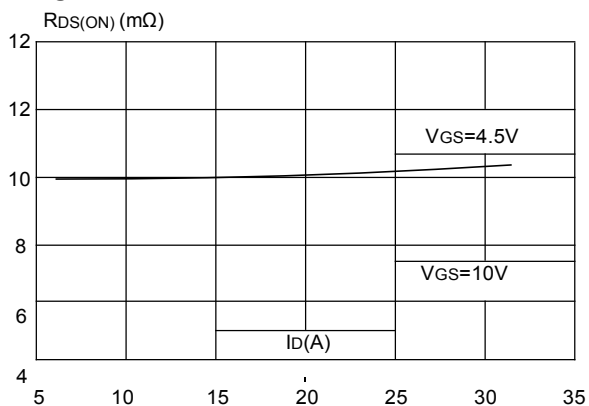


Figure 4: Body Diode Characteristics

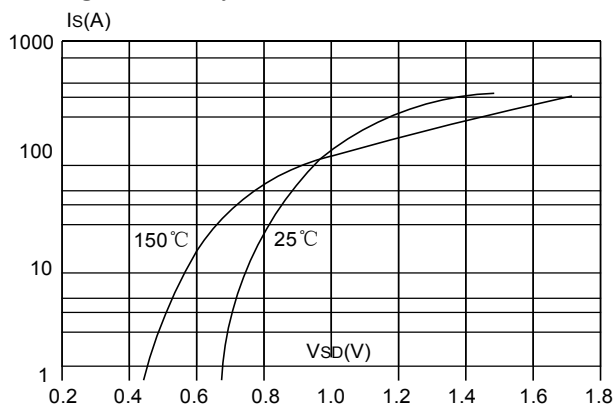


Figure 5: Gate Charge Characteristics

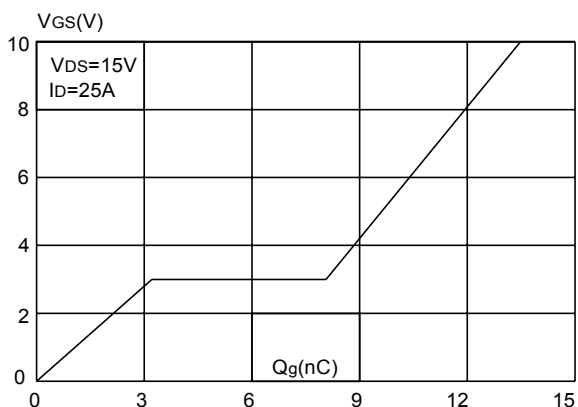
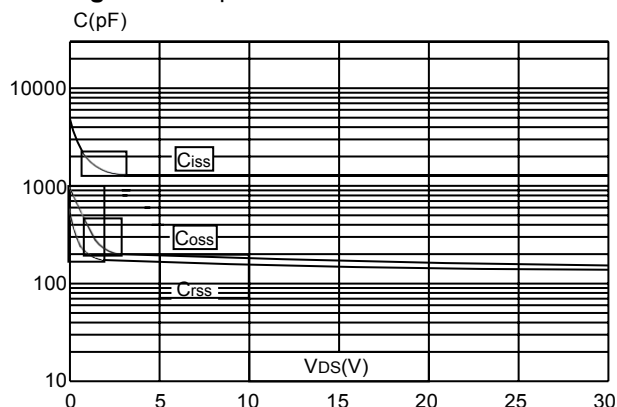


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

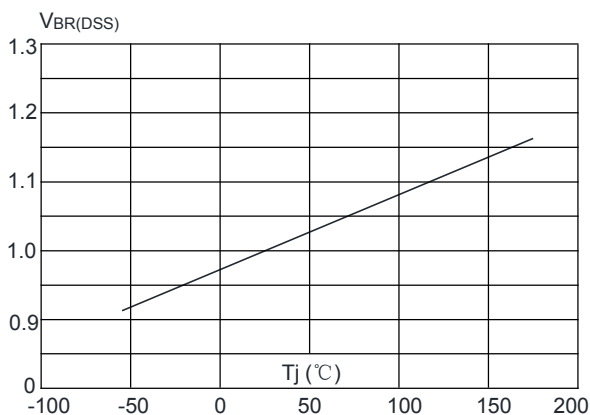


Figure 8: Normalized on Resistance vs. Junction Temperature

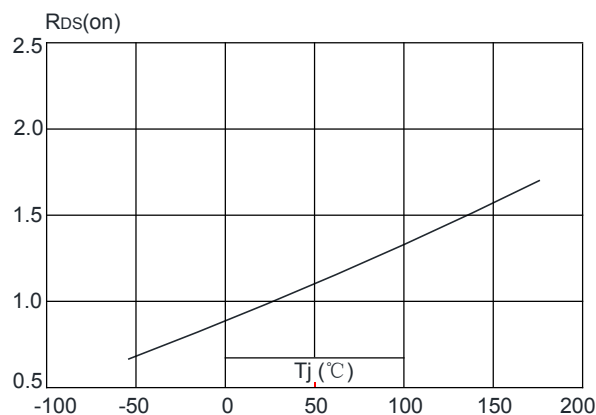
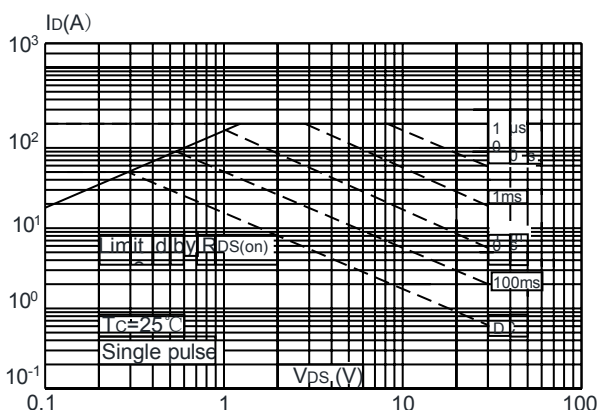


Figure 9: Maximum Safe Operating Area



Maximum Effective
Transient Thermal Impedance, Junction-to-Case

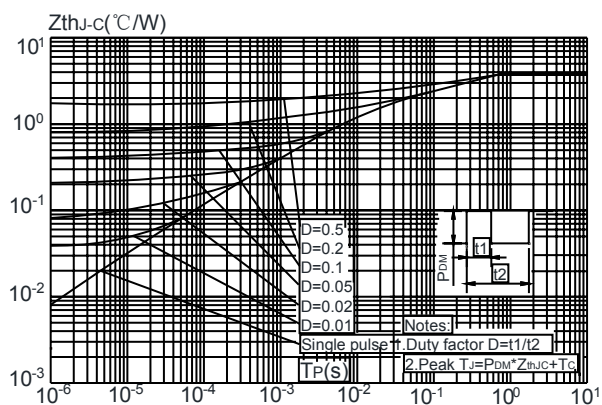
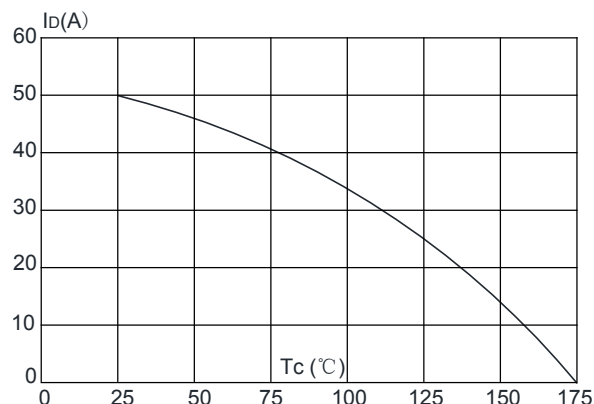


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



TEST CIRCUIT

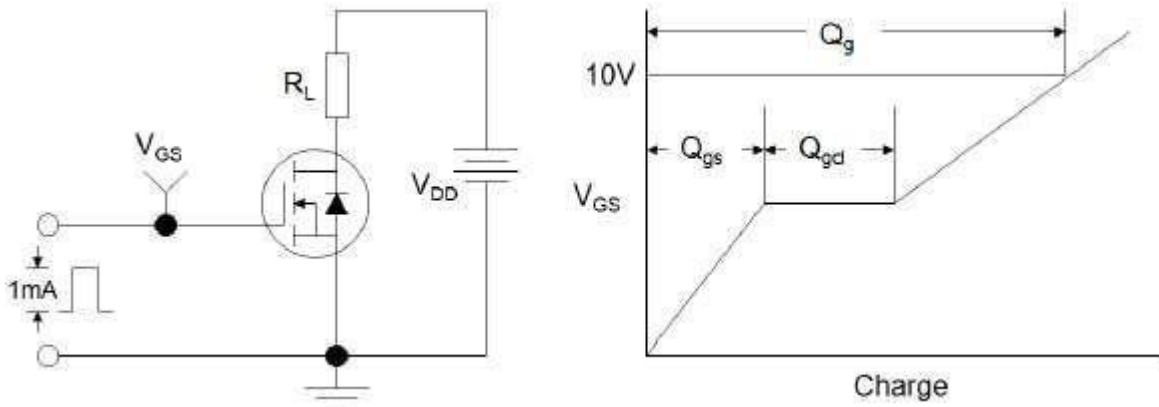


Figure1:Gate Charge Test Circuit & Waveform

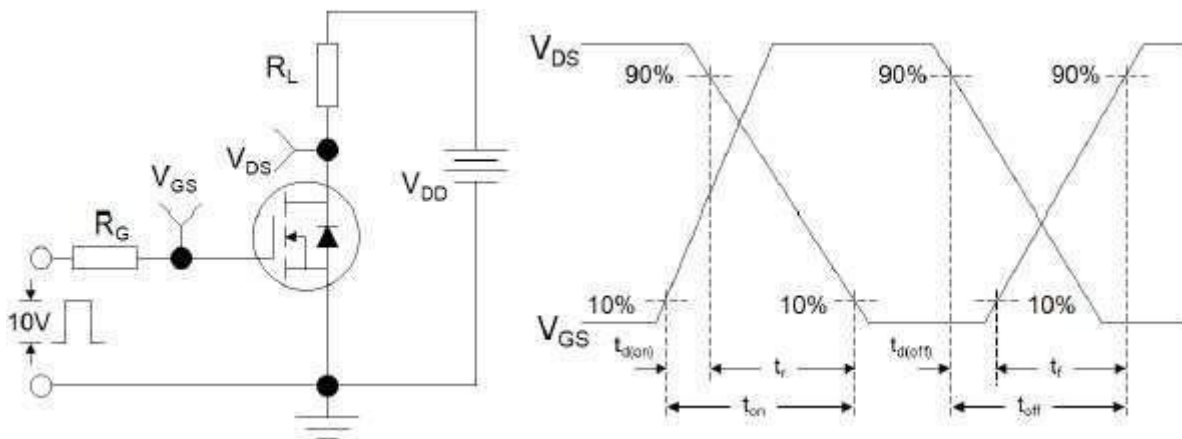


Figure 2: Resistive Switching Test Circuit & Waveforms

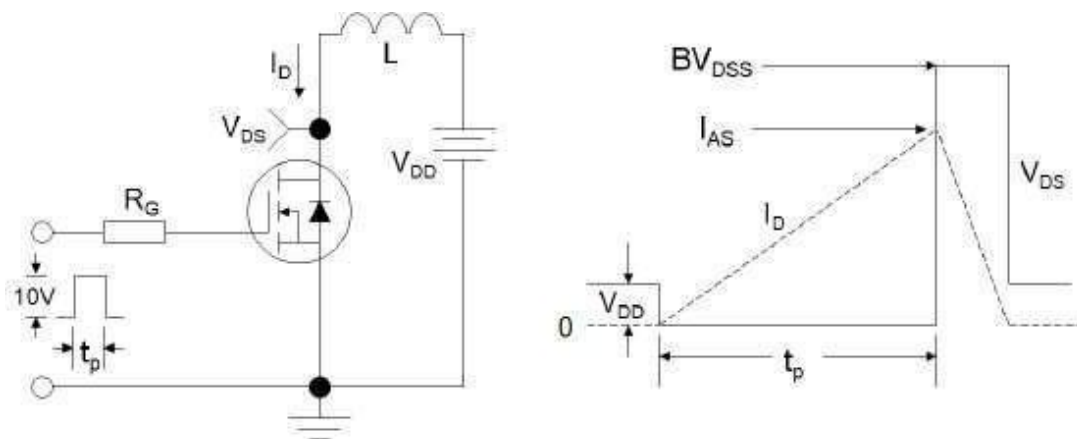
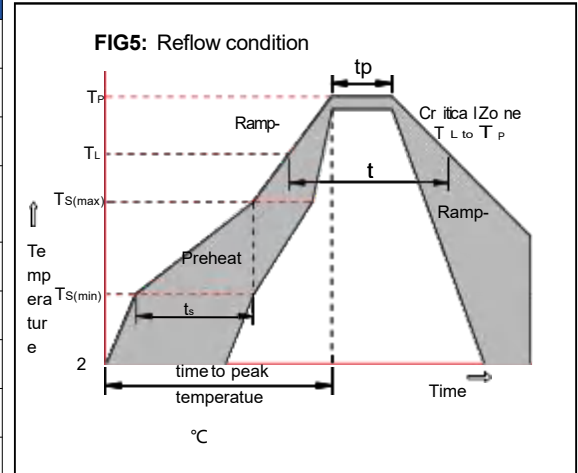


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

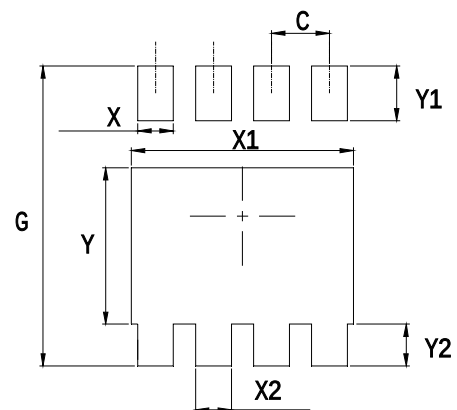
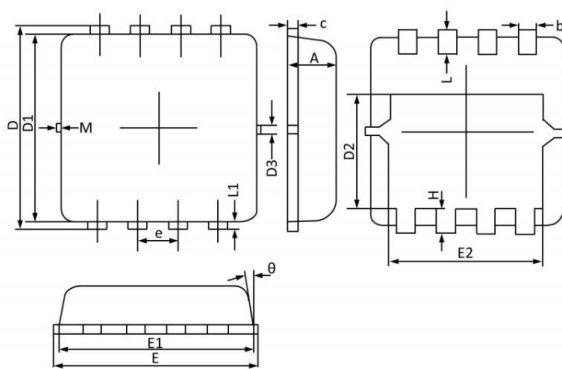
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

PDFN3X3 Package Information



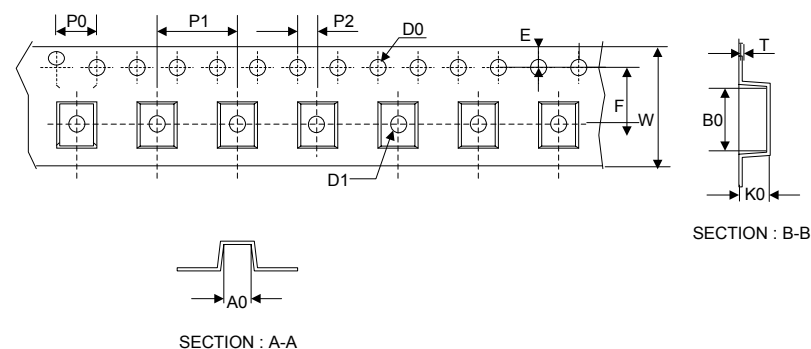
DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.70	0.75	0.80	b	0.25	0.30	0.35
C	0.10	0.15	0.25	D	3.25	3.35	3.45
D1	3.00	3.10	3.20	D2	1.78	1.88	1.98
D3	--	0.13	--	E	3.20	3.30	3.40
E1	3.00	3.15	3.20	E2	2.39	2.49	2.59
e	0.65BSC			H	0.30	0.39	0.50
L	0.30	0.40	0.50	L1	--	0.13	--
theta	--	10°	12°	M	*	*	0.15

Dimensions	Value (in mm)
C	0.65
G	3.60
X	0.40
X1	2.60
X2	0.40
Y	1.95
Y1	0.62
Y2	0.55

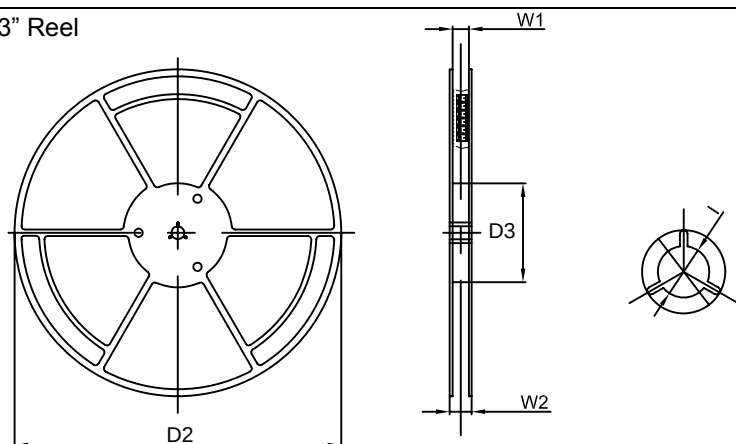
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.55±0.20
E	1.75±0.20
F	5.50±0.20
W	12.00±0.20
A0	3.90±0.20
B0	3.80±0.20
K0	1.20±0.20
T	0.20±0.20
D2	330.0±5.0
D3	100.0±4.0
W1	12.0±5.0
W2	14.0±5.0
I	13.0±2.0

13" Reel



Quantity: 5000PCS